

2-22GHz LNA with AGC

GaAs Monolithic Microwave IC in SMD leadless package

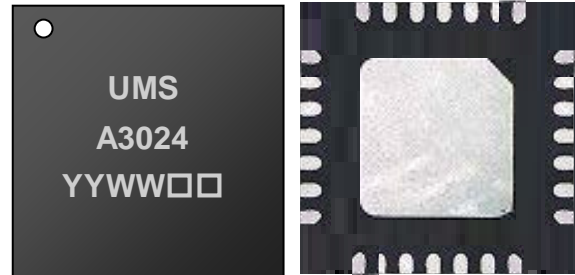
Description

The CHA3024-QGG is a distributed Low Noise Amplifier with Adjustable Gain Control (AGC) that operates between 2 and 22GHz.

It is designed for a wide range of applications, such as electronic warfare, X-band and Ku-band Point to Point Radio, and test instrumentation.

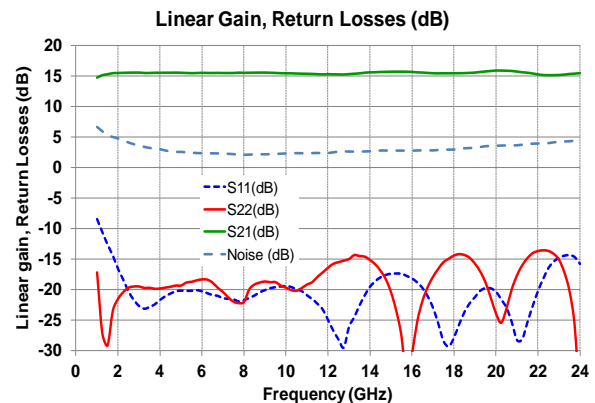
The circuit is manufactured using a 0.15µm gate length pHEMT process, with via holes through the substrate, air bridges and optical gate lithography.

It is supplied in RoHS compliant SMD package.



Main Features

- Broadband performances: 2-22GHz
- Typical Linear Gain: 15dB
- Up to 30dB AGC with Vg2
- P_{1dB}: 18dBm
- P_{sat}: 20dBm
- OIP3: 28dBm
- Typical Noise Figure: 3dB
- DC bias: V_d=5V@I_d=100mA, V_{g1}=-0.3V and V_{g2}=1.7V.
- 28L QFN 5x5
- MSL3



Main Electrical Characteristics

T_{amb}. = +25°C

Symbol	Parameter	Min	Typ	Max	Unit
Freq	Frequency range	2		22	GHz
Gain	Linear Gain	13	15	17	dB
NF	Noise Figure		3	7	dB
P _{1dB}	Output Power @1dB gain comp.	13.5	18	22.5	dBm

Electrical Characteristics

Tamb. = +25°C, Vg1 to be set in order to have Idq = 100mA, Vg2 = 1.7V

Symbol	Parameter	Min	Typ	Max	Unit
Freq	Frequency range	2		22	GHz
Gain	Linear Gain	13	15	17	dB
ΔG	Gain Control (with Vg2 variation)		30		dB
NF	Noise Figure		3	7	dB
IRL	Input Return Loss		17		dB
ORL	Output Return Loss		16		dB
P _{1dB}	Output power for 1dB Gain Compression	13.5	18	22.5	dBm
P _{sat}	Saturated output power		20		dBm
OIP3	Output Third Order Intercept		28		dBm
Idq	Quiescent current on Vd		100		mA
Vd	Supply voltage on Vd	4.5	5	5.5	V
Id	Drain current @3dB gain compression		125		mA

The values are representative of typical "test fixture" measurements as defined on the drawing in paragraph "Proposed Evaluation Board".

Absolute Maximum Ratings ⁽¹⁾T_{amb.} = +25°C

Symbol	Parameter	Values	Unit
V _d	Drain bias voltage	7V	V
I _{dq}	Drain bias current without RF	190	mA
V _{g1}	Gate bias voltage V _{g1}	-2 to 0	V
V _{g2}	Gate bias voltage V _{g2}	-2 to 2	V
V _{dg}	External drain-gate excursion	8.5	V
P _{in}	Maximum CW input power overdrive	15	dBm
T _j	Maximum Junction temperature ⁽²⁾	175	°C

⁽¹⁾ Operation of this device above anyone of these parameters may cause permanent damage: these maximum ratings parameters could not be cumulated.

These are stress ratings only, and functional operation of the device at these conditions is not implied.

⁽²⁾ Thermal Resistance channel to ground paddle (see "Device thermal performances" in the following

Recommended Operating Range ^{3, 4}

Symbol	Parameter	Values	Unit
V _d	Drain bias voltage	4 to 5	V
I _{dq}	Drain bias current	80 to 120	mA
V _{g1}	Gate bias voltage V _{g1}	-2 to 0	V
V _{g2}	Gate bias voltage V _{g2}	-2 to 2	V
P _{in}	Input power range	-20 to 12	dBm

⁽³⁾ Electrical performances are defined for specified test conditions

⁽⁴⁾ Electrical performances are not guaranteed over all recommended operating conditions

Temperature Range

T _a	Operating temperature range	-40 to +95	°C
T _{stg}	Storage temperature range	-55 to +150	°C

Typical Bias Conditions

Tamb.= +25°C

Symbol	Pin	Parameter	Values	Unit
Vg1	13	Gate control1 for the amplifier	-0.4	V
Vg2	1	Gate control2 for the amplifier	1.7	V
Vd	25	Drain Voltage	5	V

The associated drain current with no RF input power is $I_{dq} = 100\text{mA}$

This typical bias is recommended in order to get the best compromise between output power, linearity and Noise Figure performance vs. Temperature.

“Power ON” sequence

1. Ground the device
2. Set Vg1 to -1.5V
3. Set Vd to 5V (nominal value for Vd)
4. Set Vg2 to 1.7V (nominal value for Vg2)
5. Set Vg1 in the range of -0.3V for having $I_{dq} = 100\text{mA}$
6. Apply RF input power and adjust Vg2 to obtain desired gain

“Power OFF” sequence

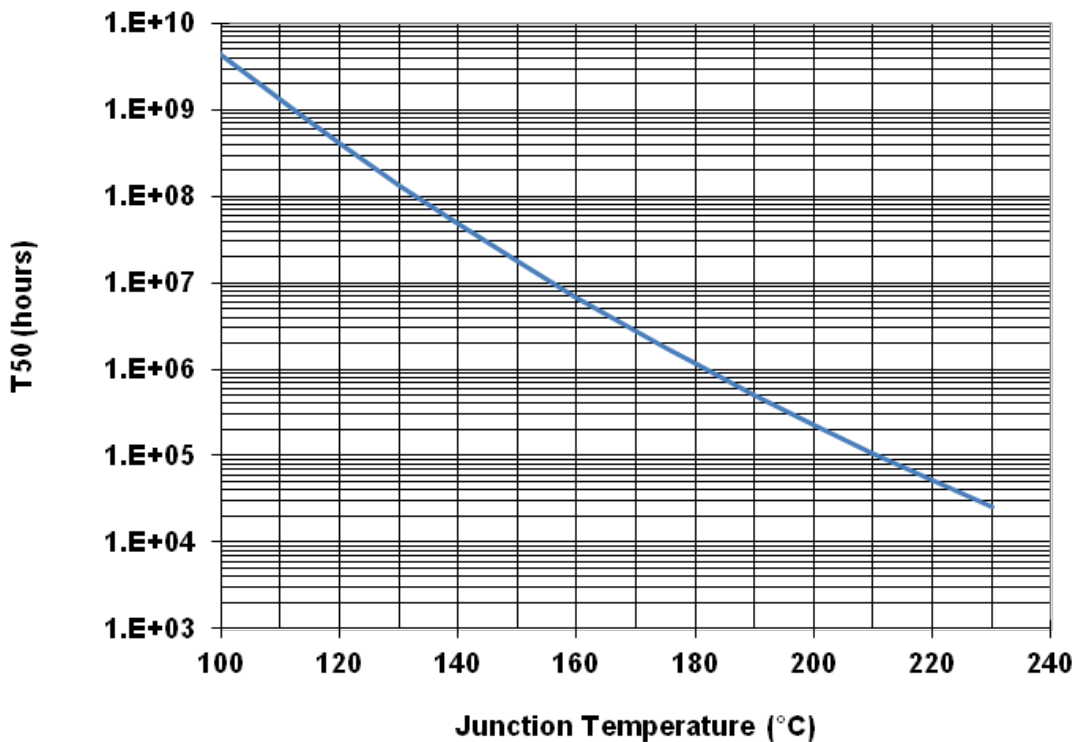
1. Set Vg2 to 1.7V
2. Turn RF power supply off
3. Set Vg1 to -1.5V in order to get $I_{dq} = 0\text{mA}$
4. Set Vg2 to 0V
5. Set Vd to 0V
6. Set Vg1 to 0V

Device thermal performances

All the figures given in this section are obtained assuming that the QFN device is only cooled down by conduction through the package thermal pad (no convection mode considered). The temperature is monitored at the package back-side interface (Tcase). The system maximum temperature must be adjusted in order to guarantee that Tjunction remains below the maximum value specified in the Absolute Maximum Ratings table. So, the system PCB must be designed to comply with this requirement.

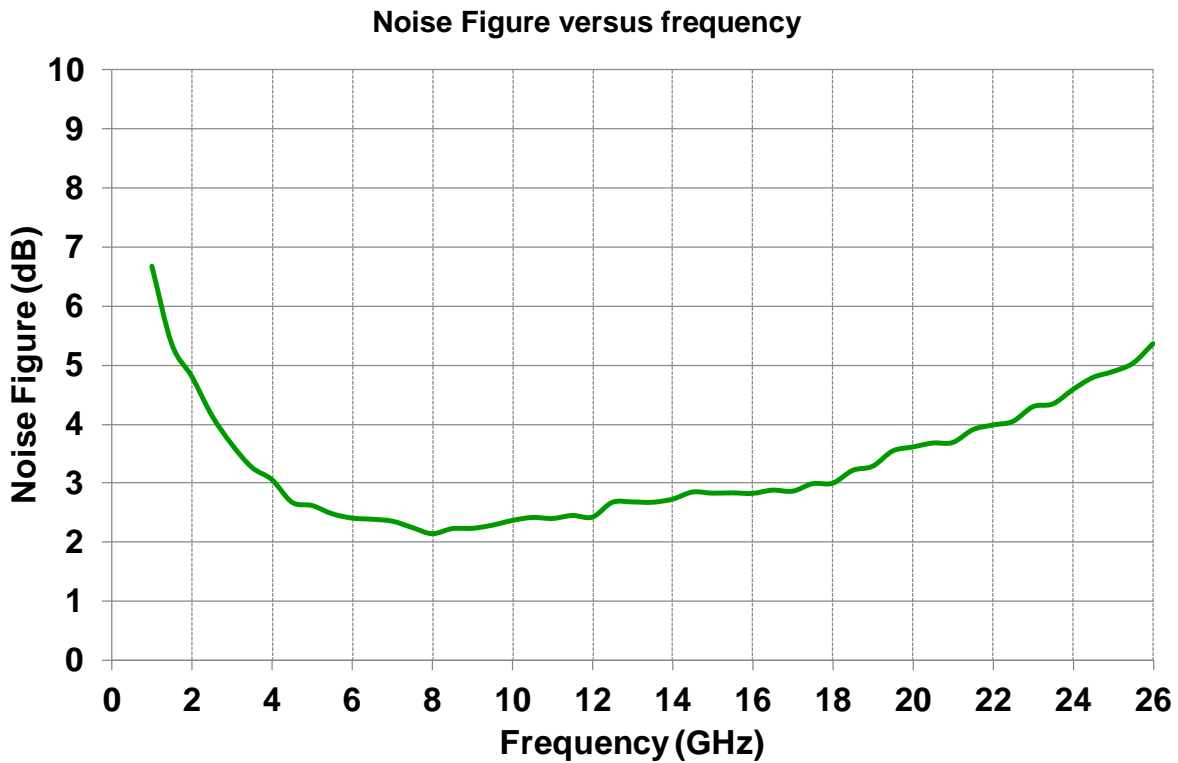
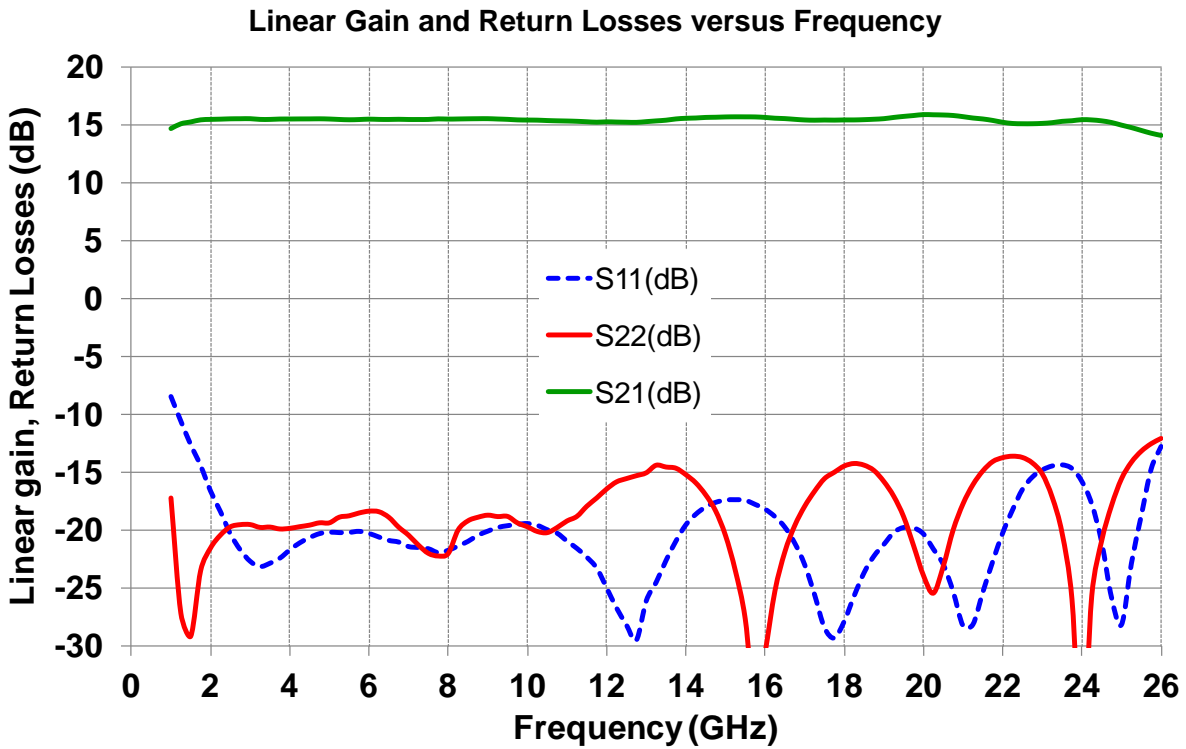
Parameter	Biasing conditions	Tjunction (°C)	RTH (°C/W)	T50 (hours)
RTH ⁽¹⁾ Thermal Resistance (Junction to Case)	Vd= 5V Id= 100mA Pdiss= 0.5W	114	57.7	8.05E+8

¹ Assuming 85°C Tcase



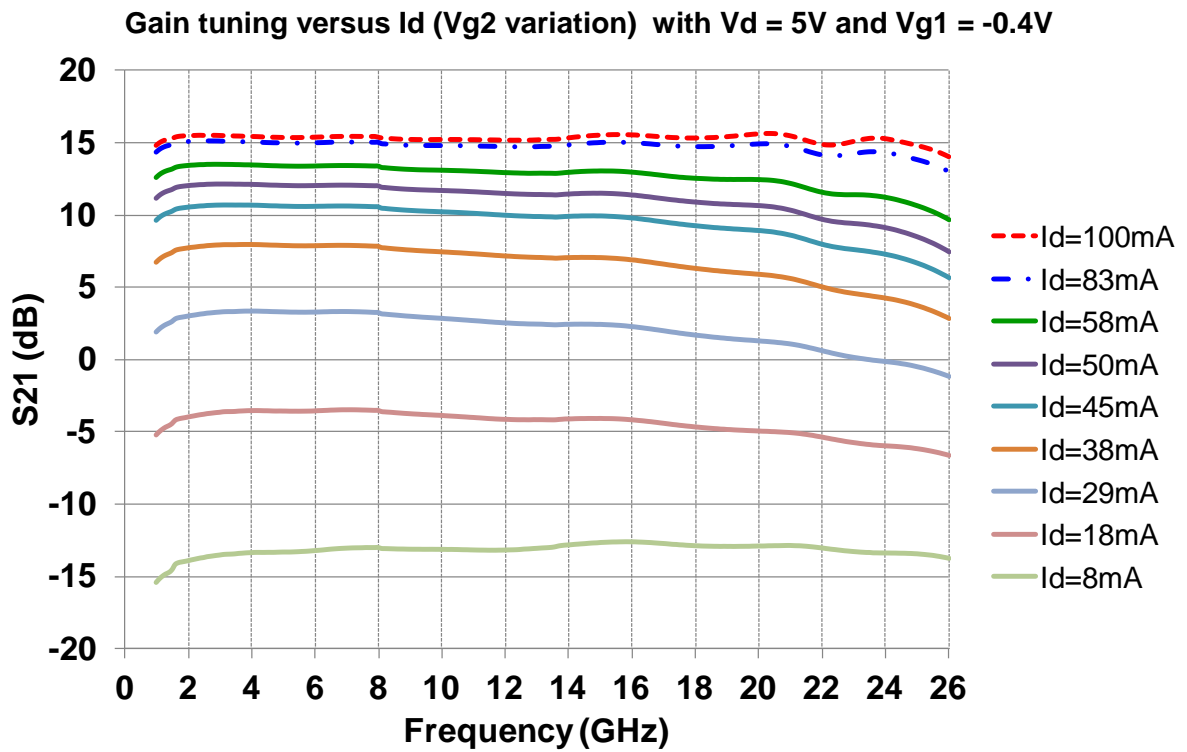
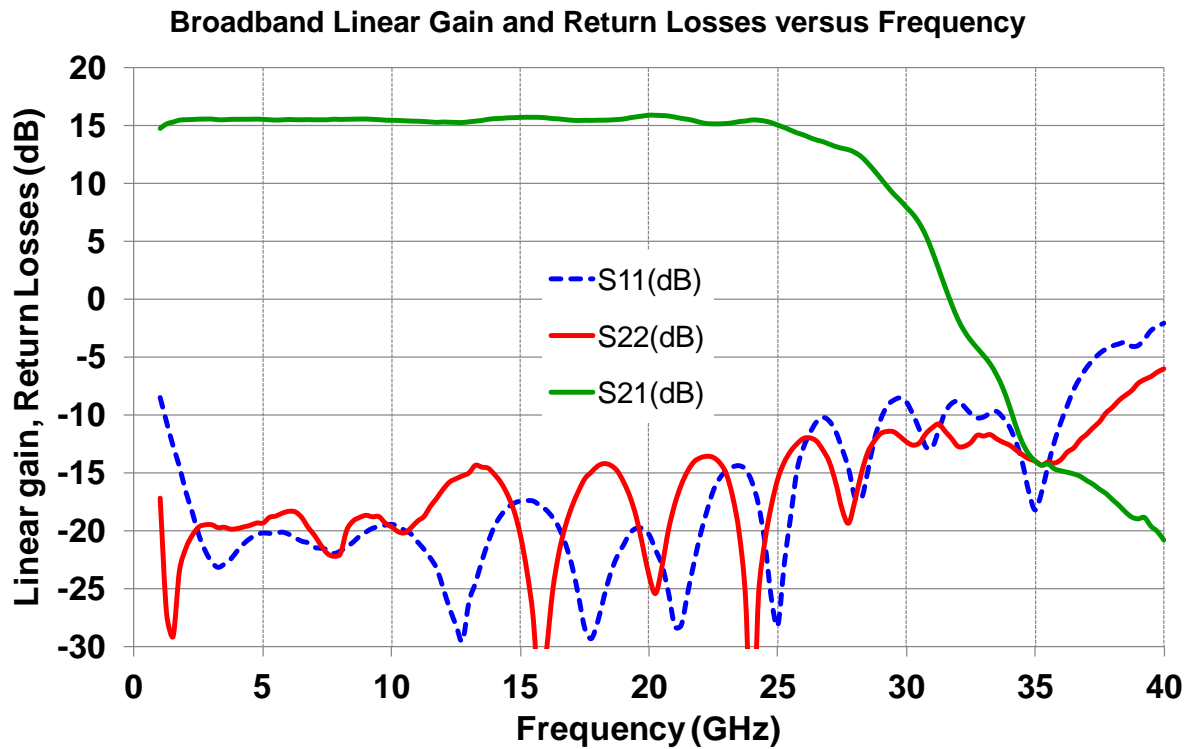
Typical Board Measurements

Tamb. = +25°C, Vd = 5V, Vg1 set in order to get Idq = 100mA, Vg2 = 1.7V



Typical Board Measurements

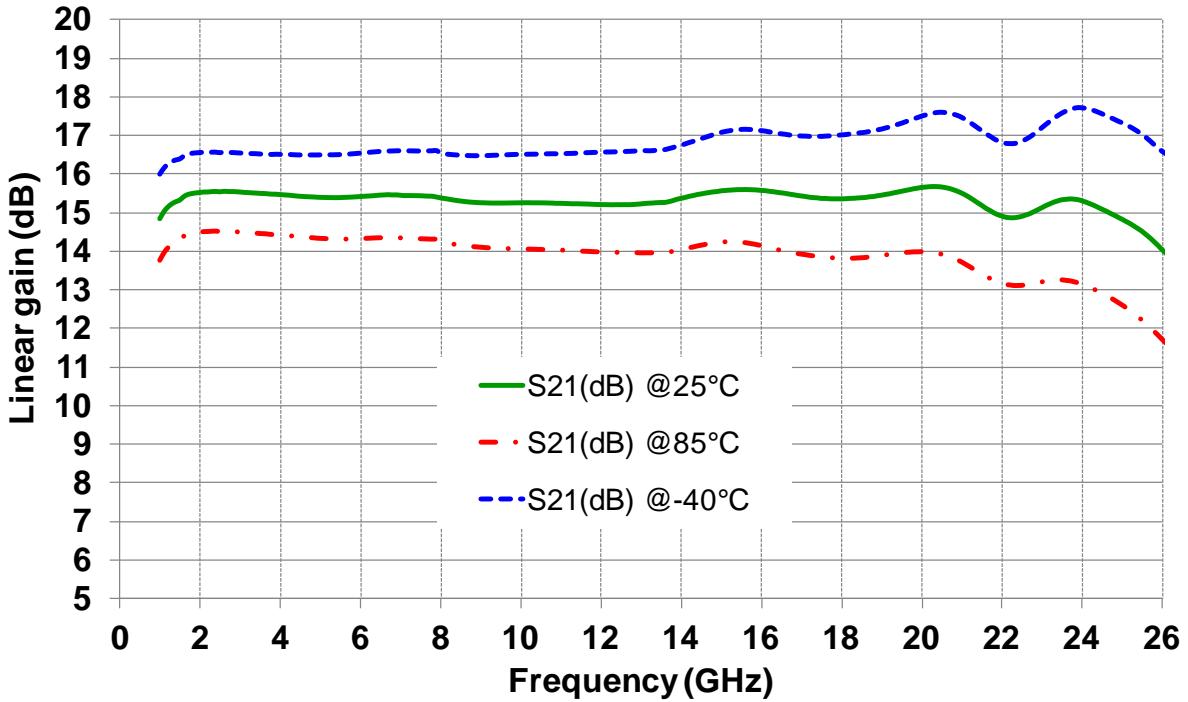
Tamb. = +25°C, Vd = 5V, Vg1 set in order to get Idq = 100mA, Vg2 = 1.7V



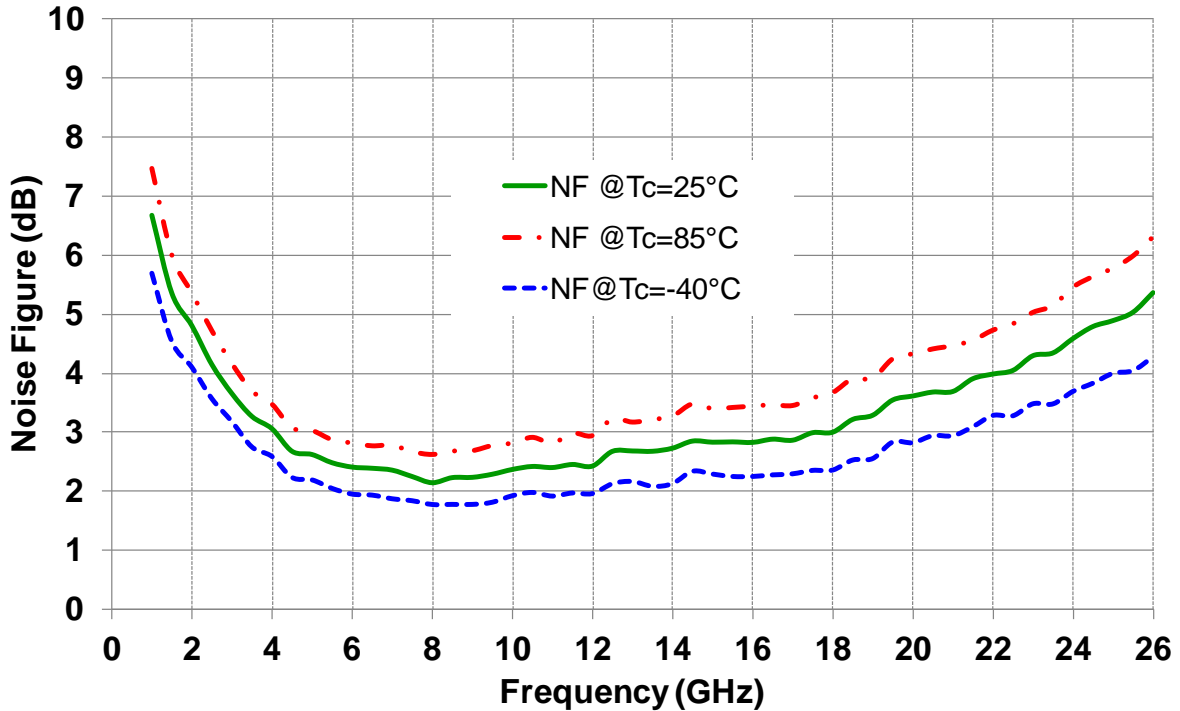
Typical Board Measurements

Tamb. = +25°C, +85°C, -40°C, Vd = 5V, Vg1 set in order to get Idq = 100mA, Vg2 = 1.7V
 Vg1 and Vg2 remain constant versus temperature.

Linear Gain vs Temperature

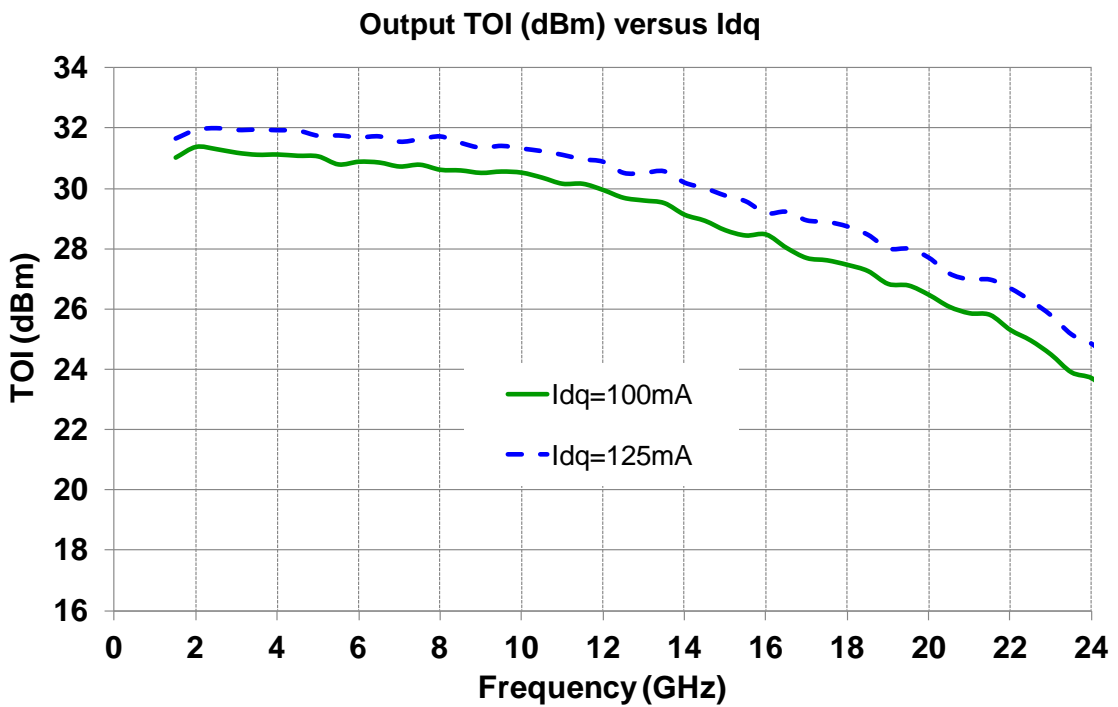
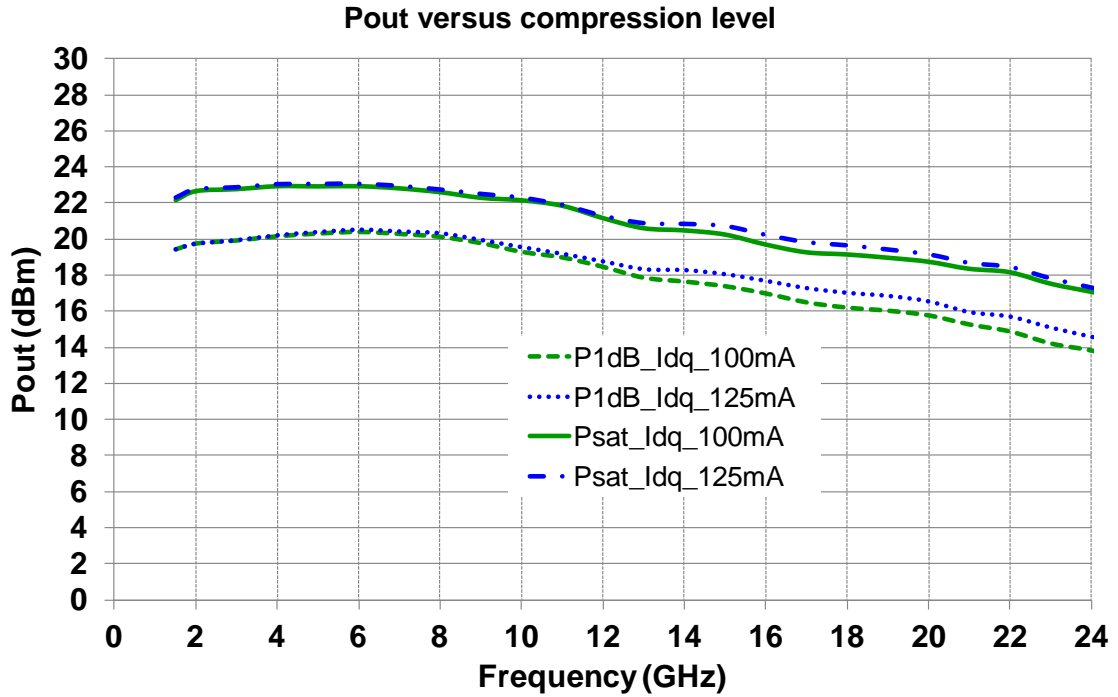


Noise Figure vs Temperature



Typical Board Measurements

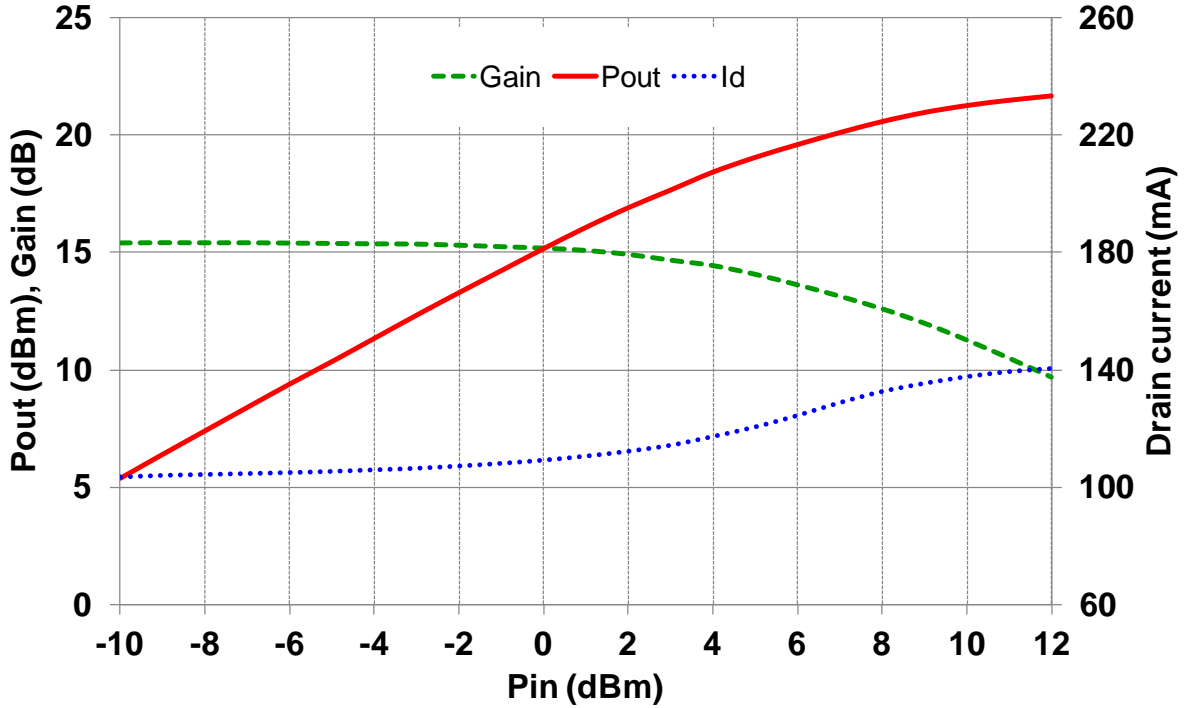
Tamb. = +25°C, Vd = 5V, Vg1 set in order to get Idq = 100/125 mA , Vg2 = 1.7V



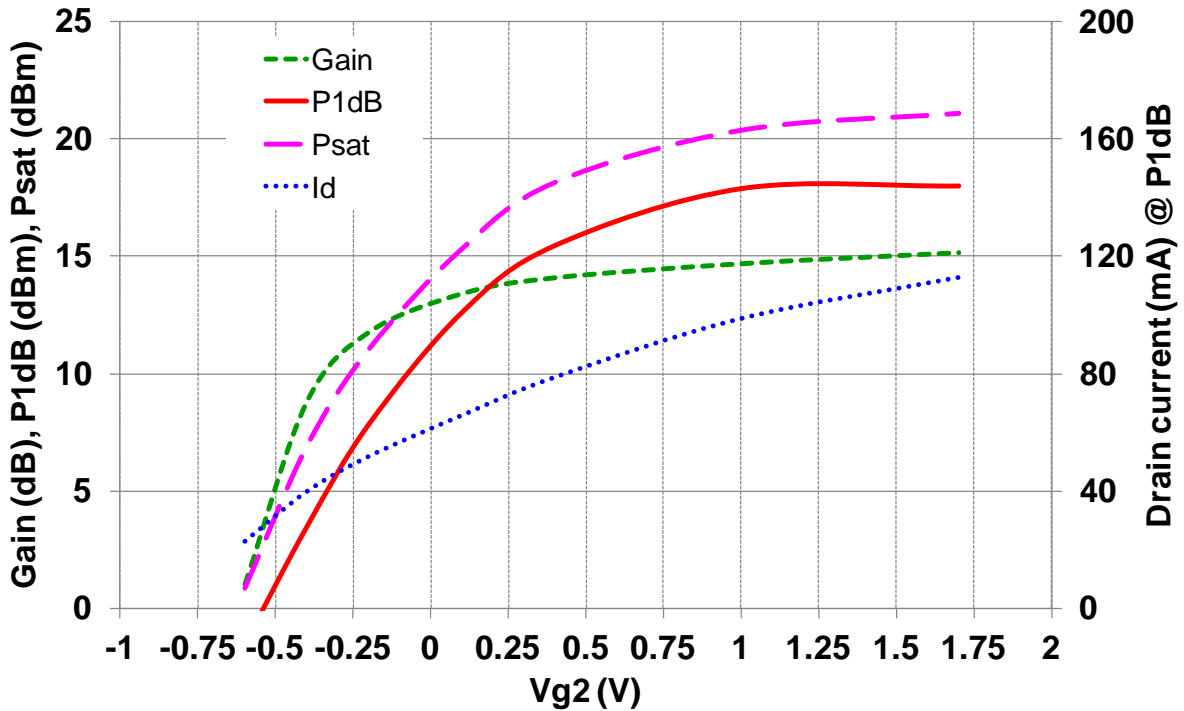
Typical Board Measurements

Tamb. = +25°C, Vd = 5V, Vg1 set in order to get Idq = 100mA, Vg2 = 1.7V

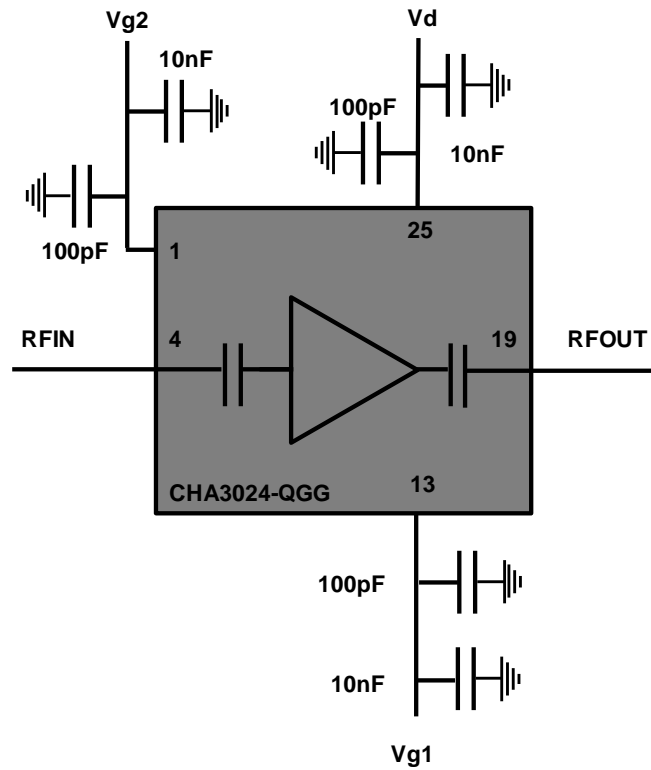
Main Performance versus Pin (dBm) @ Freq = 12GHz



Main Performance versus Vg2 (V) @ Freq = 12GHz



Application Circuit:



Depending on the board, additional capacitors such as 1 μ F may be added on each biasing access if necessary, for better low frequency decoupling.

Pin Description:

Pin	Symbol	Description
5,18, 29 (exposed PAD)	GND	Must be grounded properly, internal connections to ground are made
2,3,6,7,8,9,10,11,12,14,15,16, 17,20,21,22,23,24,26,27,28	NC	No internal connections
4	RF IN	RF input
13	VG1	Gate voltage, bias network required
19	RF OUT	RF output
25	VD	Drain voltage, bias network required
1	VG2	Gate voltage bias network required

UMS recommends also to ground Pin 2,3,5,6,7,15,16,17,18,20,21 (see proposed footprint p14).

Proposed Evaluation Board

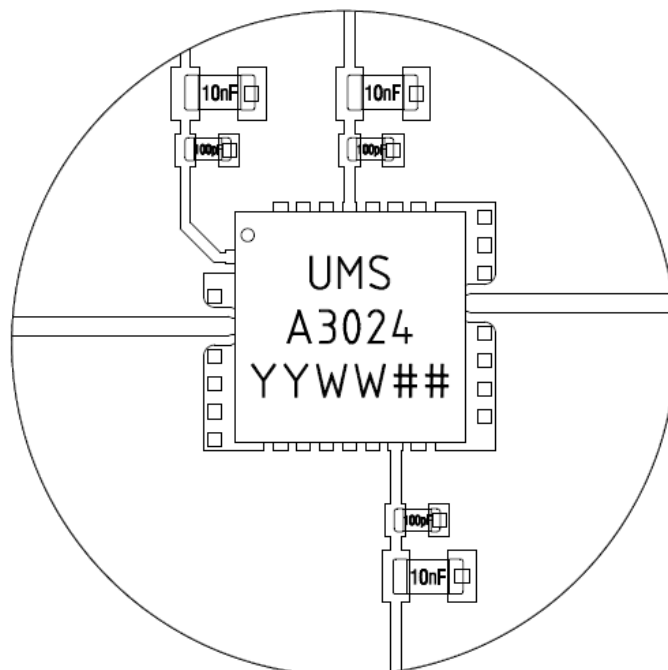
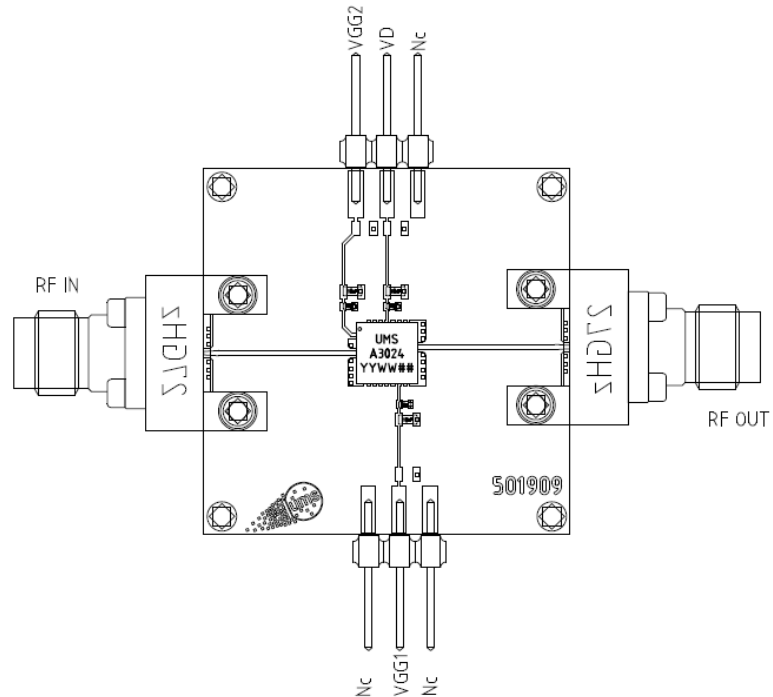
Compatible with the proposed footprint on page p14.

Top dielectric material is Rogers 4003 / 8mils or equivalent substrate.

Decoupling capacitors at first level are 100pF.

Decoupling capacitors at second level are 10nF.

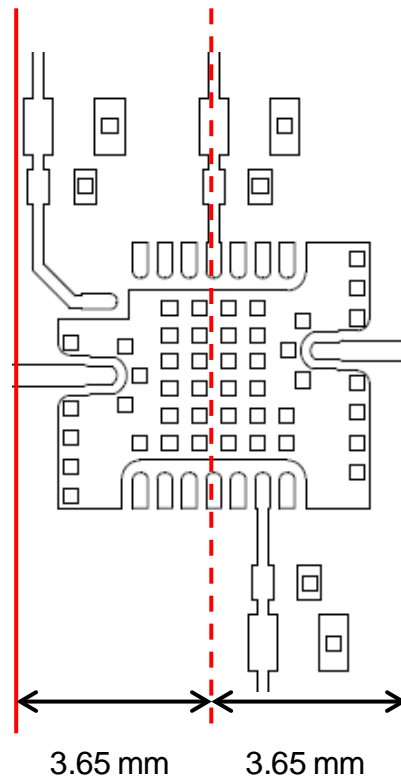
Additional capacitors such as 1 μ F may also be added on each DC access.



Package footprint and Definition of the measurements planes

The reference planes used for the provided measurements are symmetrical from the symmetrical axis of the package (see drawing beside). The input and output reference planes are located at 3.65 mm offset (input wise and output wise respectively) from this axis.

From the edge of the QFN, the reference planes are 1.15mm apart.



Package Information

Parameter	Value
Package body material	RoHS-compliant
	Low stress Injection Molded Plastic
Lead finish	100% matte tin (Sn)
MSL Rating	MSL3

Recommended package footprint

Refer to the application note AN0017 available at <http://www.ums-gaas.com> for package footprint recommendations.

SMD mounting procedure

For the mounting process standard techniques involving solder paste and a suitable reflow process can be used. For further details, see application note AN0017.

Recommended environmental management

UMS products are compliant with the regulation in particular with the directives RoHS N°2011/65 and REACH N°1907/2006. More environmental data are available in the application note AN0019 also available at <http://www.ums-gaas.com>.

Recommended ESD management

Refer to the application note AN0020 available at <http://www.ums-gaas.com> for ESD sensitivity and handling recommendations for the UMS package products.

Ordering Information

QFN 28L 5x5 package:

CHA3024-QGG/XY

Stick: XY = 20

Tape & reel: XY = 21

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